

< IGBT MODULES >

# CM1400DUC-24NF

HIGH POWER SWITCHING USE  
INSULATED TYPE



**dual switch (Half-Bridge)**

Collector current  $I_C$  ..... **1 4 0 0 A**  
 Collector-emitter voltage  $V_{CES}$  ..... **1 2 0 0 V**  
 Maximum junction temperature  $T_{jmax}$  ..... **1 5 0 °C**

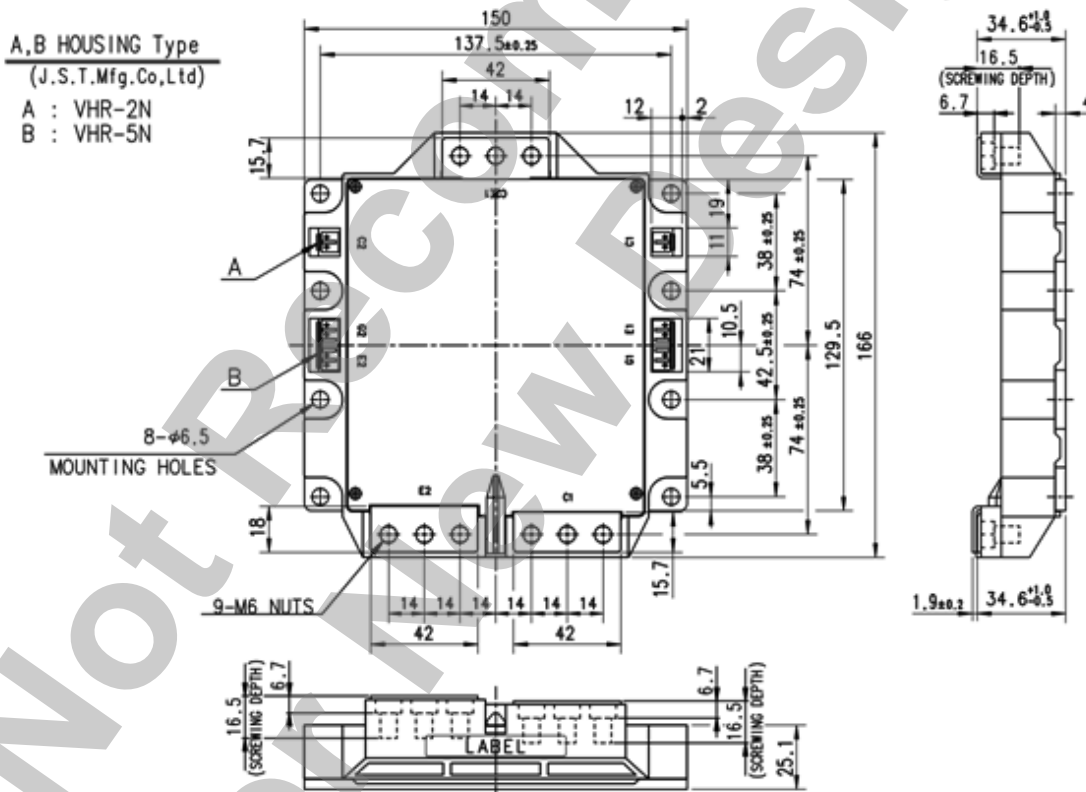
- Flat base Type
- Copper base plate (non-plating)
- RoHS Directive compliant
- Recognized under UL1557, File E323585

## APPLICATION

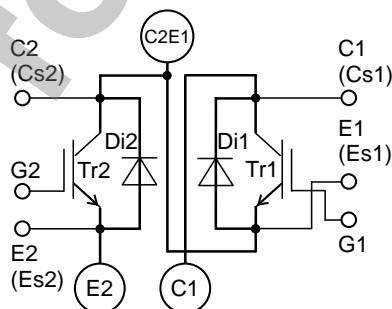
Wind power, Photovoltaic (Solar) power, AC Motor Control, Motion/Servo Control, Power supply, etc.

## OUTLINE DRAWING & INTERNAL CONNECTION

Dimension in mm



### INTERNAL CONNECTION



Tolerance otherwise specified

Division of Dimension	Tolerance
0.5 to 3	±0.2
over 3 to 6	±0.3
over 6 to 30	±0.5
over 30 to 120	±0.8
over 120 to 400	±1.2

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MAXIMUM RATINGS ( $T_j=25\text{ }^\circ\text{C}$ , unless otherwise specified)

Symbol	Item	Conditions	Rating	Unit
$V_{CES}$	Collector-emitter voltage	G-E short-circuited	1200	V
$V_{GES}$	Gate-emitter voltage	C-E short-circuited	$\pm 20$	V
$I_C$	Collector current	DC, $T_C=94\text{ }^\circ\text{C}$ (Note2, 4)	1400	A
$I_{CRM}$		Pulse, Repetitive (Note3)	2800	
$P_{tot}$	Total power dissipation	$T_C=25\text{ }^\circ\text{C}$ (Note2, 4)	8925	W
$I_E$ (Note1)	Emitter current	DC (Note2)	1400	A
$I_{ERM}$ (Note1)		Pulse, Repetitive (Note3)	2800	
$V_{isol}$	Isolation voltage	Terminals to base plate, RMS, f=60 Hz, AC 1 min	2500	V
$T_j$	Junction temperature	-	-40 ~ +150	$^\circ\text{C}$
$T_{stg}$	Storage temperature	(Note7)	-40 ~ +125	

ELECTRICAL CHARACTERISTICS ( $T_j=25\text{ }^\circ\text{C}$ , unless otherwise specified)

Symbol	Item	Conditions	Limits			Unit	
			Min.	Typ.	Max.		
$I_{CES}$	Collector-emitter cut-off current	$V_{CE}=V_{CES}$ , G-E short-circuited	-	-	1.0	mA	
$I_{GES}$	Gate-emitter leakage current	$V_{GE}=V_{GES}$ , C-E short-circuited	-	-	1.5	$\mu\text{A}$	
$V_{GE(th)}$	Gate-emitter threshold voltage	$I_C=140\text{ mA}$ , $V_{CE}=10\text{ V}$	6	7	8	V	
$V_{CESat}$	Collector-emitter saturation voltage	$I_C=1400\text{ A}$ , $V_{GE}=15\text{ V}$ (Note5) Refer to the figure of test circuit	$T_j=25\text{ }^\circ\text{C}$	-	1.8	2.5	V
			$T_j=125\text{ }^\circ\text{C}$	-	2.0	-	
$C_{ies}$	Input capacitance	$V_{CE}=10\text{ V}$ , G-E short-circuited	-	-	220	nF	
$C_{oes}$	Output capacitance		-	-	25		
$C_{res}$	Reverse transfer capacitance		-	-	4.7		
$Q_G$	Gate charge	$V_{CC}=600\text{ V}$ , $I_C=1400\text{ A}$ , $V_{GE}=15\text{ V}$	-	7200	-	nC	
$t_{d(on)}$	Turn-on delay time	$V_{CC}=600\text{ V}$ , $I_C=1400\text{ A}$ , $V_{GE}=\pm 15\text{ V}$ , $R_G=0.22\text{ }\Omega$ , Inductive load	-	-	800	ns	
$t_r$	Rise time		-	-	300		
$t_{d(off)}$	Turn-off delay time		-	-	1000		
$t_f$	Fall time		-	-	300		
$V_{EC}$ (Note1)	Emitter-collector voltage	$I_E=1400\text{ A}$ , G-E short-circuited, Refer to the figure of test circuit (Note5)	$T_j=25\text{ }^\circ\text{C}$	-	2.5	3.2	V
			$T_j=125\text{ }^\circ\text{C}$	-	2.1	-	
$t_{rr}$ (Note1)	Reverse recovery time	$V_{CC}=600\text{ V}$ , $I_E=1400\text{ A}$ , $V_{GE}=\pm 15\text{ V}$ , $R_G=0.22\text{ }\Omega$ , Inductive load	-	-	700	ns	
$Q_{rr}$ (Note1)	Reverse recovery charge	$R_G=0.22\text{ }\Omega$ , Inductive load	-	90	-	$\mu\text{C}$	
$E_{on}$	Turn-on switching energy per pulse	$V_{CC}=600\text{ V}$ , $I_C=I_E=1400\text{ A}$ ,	-	122.8	-	mJ	
$E_{off}$	Turn-off switching energy per pulse	$V_{GE}=\pm 15\text{ V}$ , $R_G=0.22\text{ }\Omega$ , $T_j=150\text{ }^\circ\text{C}$ ,	-	161.2	-		
$E_{rr}$ (Note1)	Reverse recovery energy per pulse	Inductive load	-	136.9	-	mJ	
$R_{CC+EE}$	Internal lead resistance	Main terminals-chip, per switch, $T_C=25\text{ }^\circ\text{C}$ (Note4)	-	0.286	-	m $\Omega$	
$r_g$	Internal gate resistance	Per switch	-	1.0	-	$\Omega$	

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**THERMAL RESISTANCE CHARACTERISTICS**

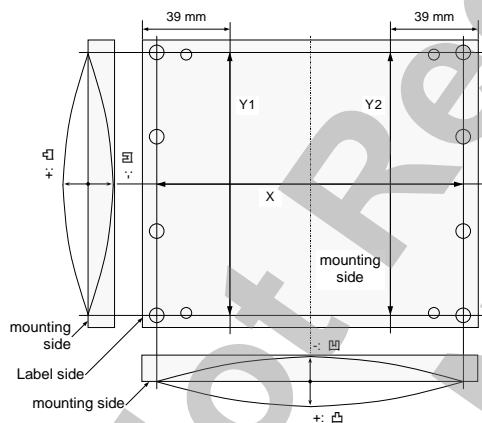
Symbol	Item	Conditions	Limits			Unit
			Min.	Typ.	Max.	
$R_{th(j-c)Q}$	Thermal resistance	Junction to case, per Inverter IGBT (Note4)	-	-	14	K/kW
$R_{th(j-c)D}$		Junction to case, per Inverter DIODE (Note4)	-	-	23	
$R_{th(c-s)}$	Contact thermal resistance	Case to heat sink, per 1/2 module, Thermal grease applied (Note4, 6)	-	12	-	K/kW

**MECHANICAL CHARACTERISTICS**

Symbol	Item	Conditions	Limits			Unit
			Min.	Typ.	Max.	
$M_t$	Mounting torque	Main terminals M 6 screw	3.5	4.0	4.5	N·m
$M_s$		Mounting to heat sink M 6 screw	3.5	4.0	4.5	N·m
$d_s$	Creepage distance	Terminal to terminal	24	-	-	mm
		Terminal to base plate	33	-	-	
$d_a$	Clearance	Terminal to terminal	14	-	-	mm
		Terminal to base plate	33	-	-	
m	mass	-	-	1450	-	g
$e_c$	Flatness of base plate	On the centerline X, Y1, Y2 (Note8)	-50	-	+100	$\mu$ m

Note1. Represent ratings and characteristics of the anti-parallel, emitter-collector free wheeling diode (DIODE).

2. Junction temperature ( $T_j$ ) should not increase beyond  $T_{jmax}$  rating.
3. Pulse width and repetition rate should be such that the device junction temperature ( $T_j$ ) dose not exceed  $T_{jmax}$  rating.
4. Case temperature ( $T_c$ ) and heat sink temperature ( $T_s$ ) are defined on the each surface (mounting side) of base plate and heat sink just under the chips. Refer to the figure of chip location.  
The heat sink thermal resistance should measure just under the chips.
5. Pulse width and repetition rate should be such as to cause negligible temperature rise. Refer to the figure of test circuit.
6. Typical value is measured by using thermally conductive grease of  $\lambda=0.9$  W/(m·K).
7. The operation temperature is restrained by the permission temperature of female connector housing.
8. Base plate (mounting side) flatness measurement points (X, Y1 and Y2) are as follows of the following figure.



9. The company name and product names herein are the trademarks and registered trademarks of the respective companies.

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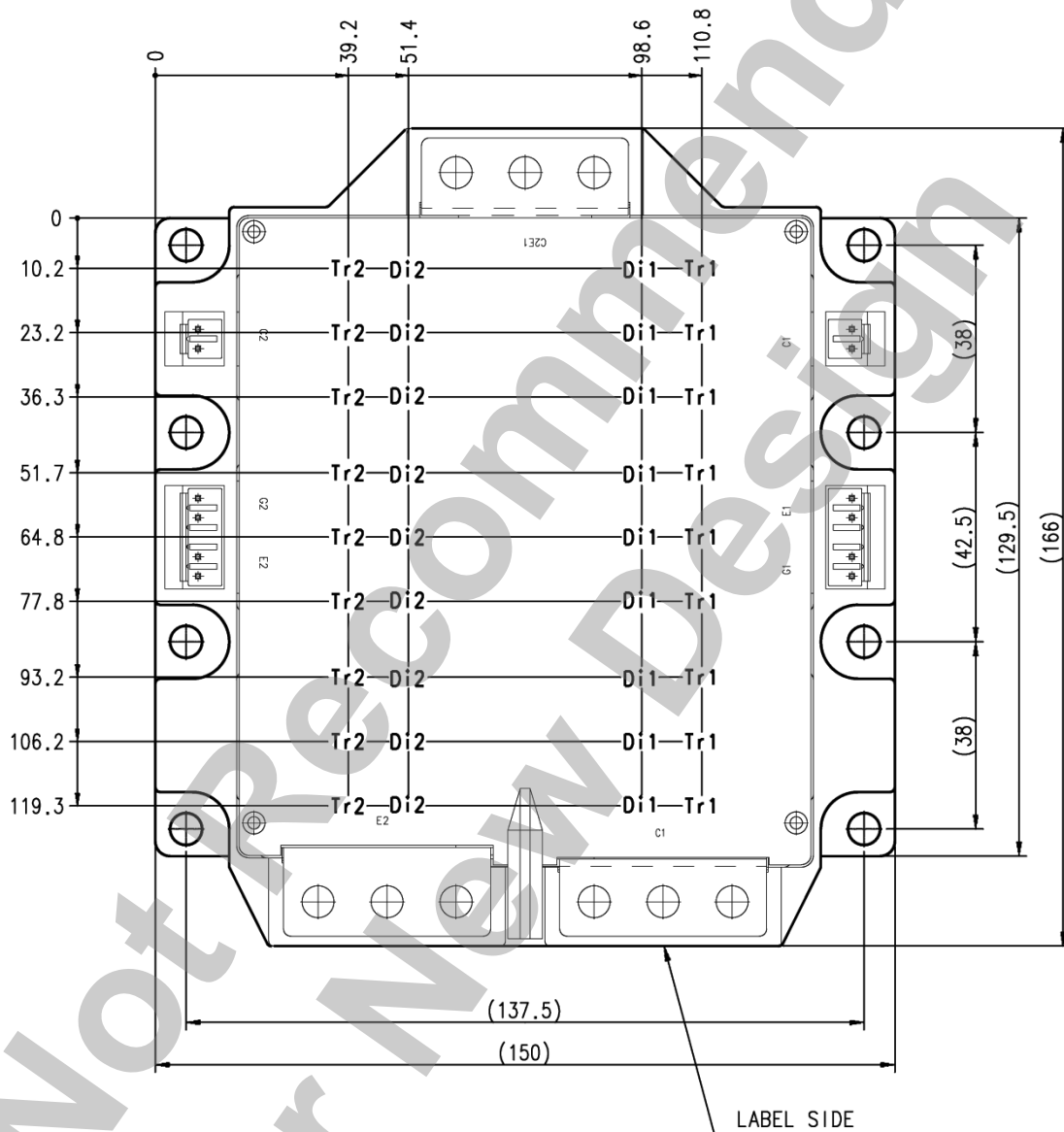
INSULATED TYPE

RECOMMENDED OPERATING CONDITIONS

Symbol	Item	Conditions	Limits			Unit
			Min.	Typ.	Max.	
$V_{CC}$	(DC) Supply voltage	Applied across C1-E2 terminals	-	600	800	V
$V_{GEon}$	Gate (-emitter drive) voltage	Applied across G1-Es1/G2-Es2 terminals	13.5	15.0	16.5	V
$R_G$	External gate resistance	Per switch	0.22	-	2.2	$\Omega$

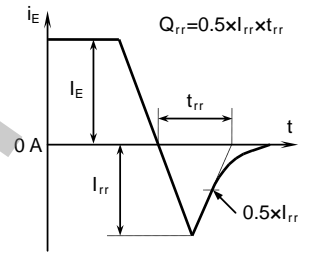
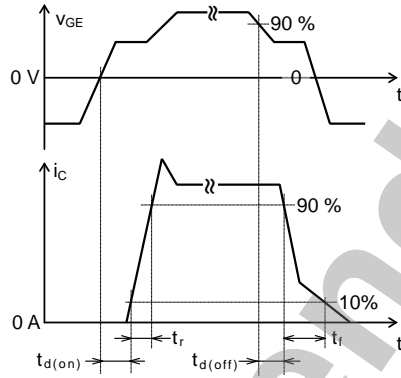
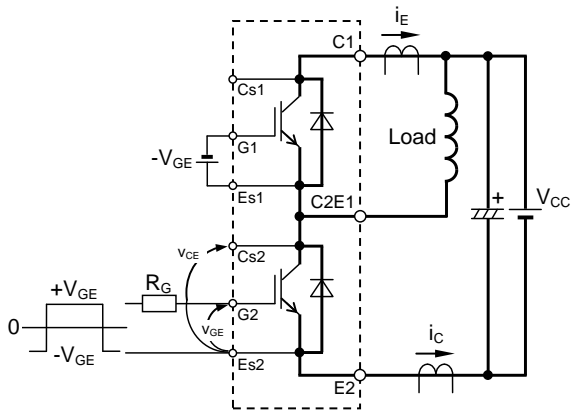
CHIP LOCATION (Top view)

Dimension in mm, tolerance:  $\pm 1$  mm



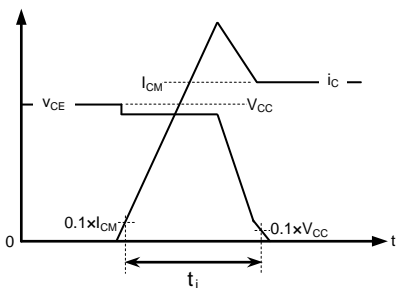
Tr1/Tr2: IGBT, Di1/Di2: DIODE

TEST CIRCUIT AND WAVEFORMS

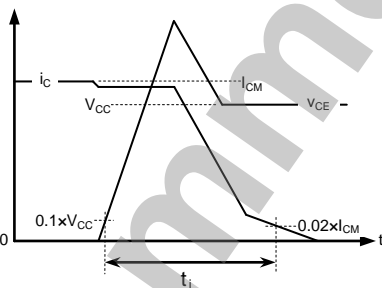


Switching characteristics test circuit and waveforms

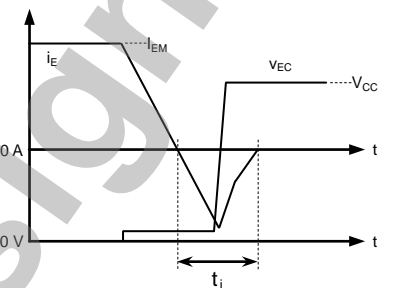
$t_{rr}$ ,  $Q_{rr}$  test waveform



IGBT Turn-on switching energy



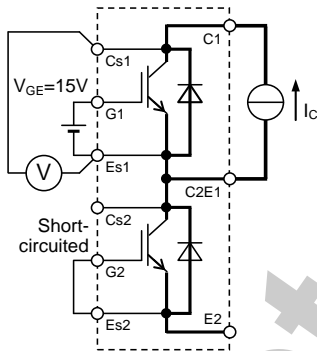
IGBT Turn-off switching energy



DIODE Reverse recovery energy

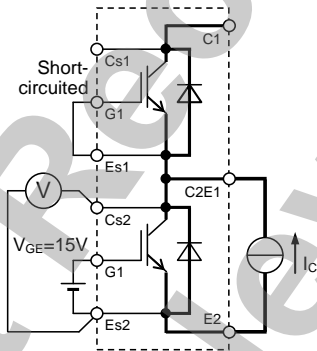
Turn-on / Turn-off switching energy and Reverse recovery energy test waveforms (Integral time instruction drawing)

TEST CIRCUIT

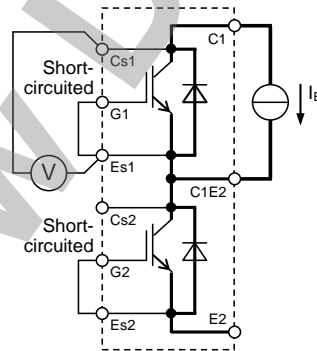


Tr1

$V_{CEsat}$  test circuit

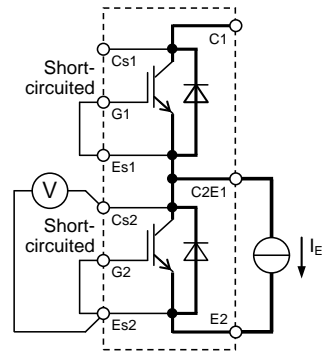


Tr2



Di1

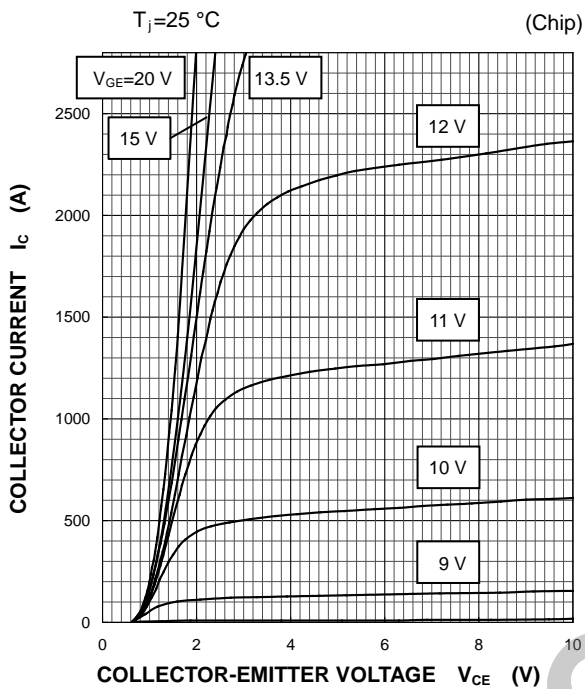
$V_{EC}$  test circuit



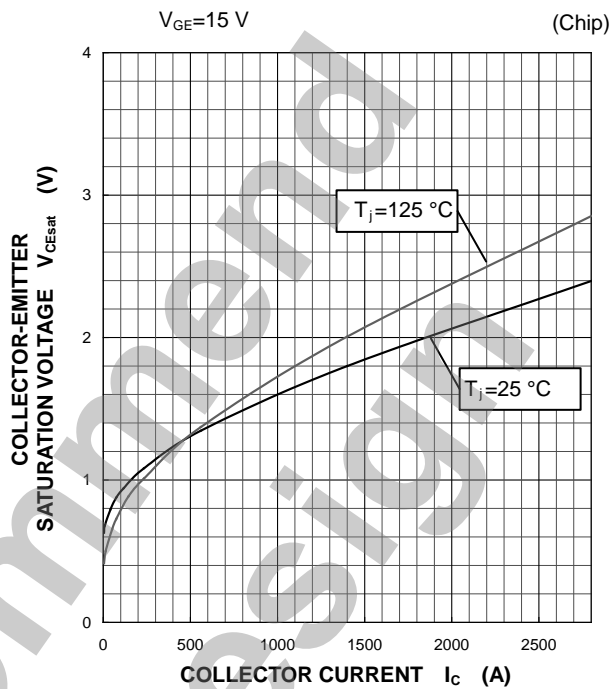
Di2

PERFORMANCE CURVES

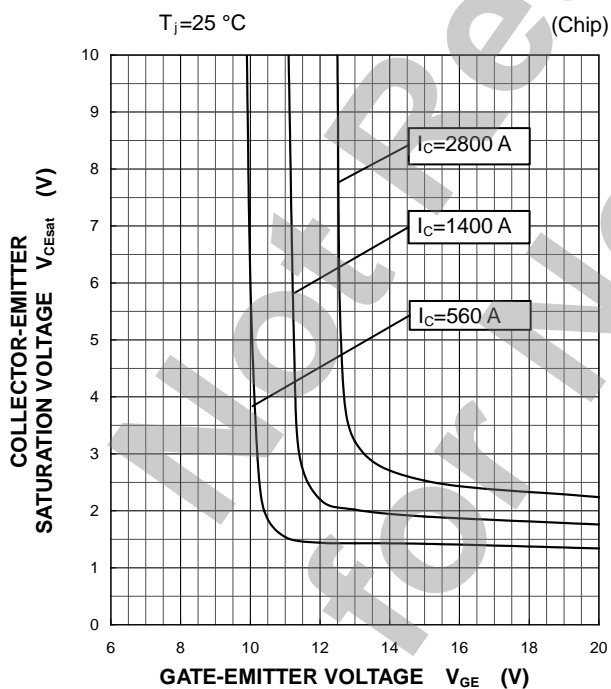
OUTPUT CHARACTERISTICS  
(TYPICAL)



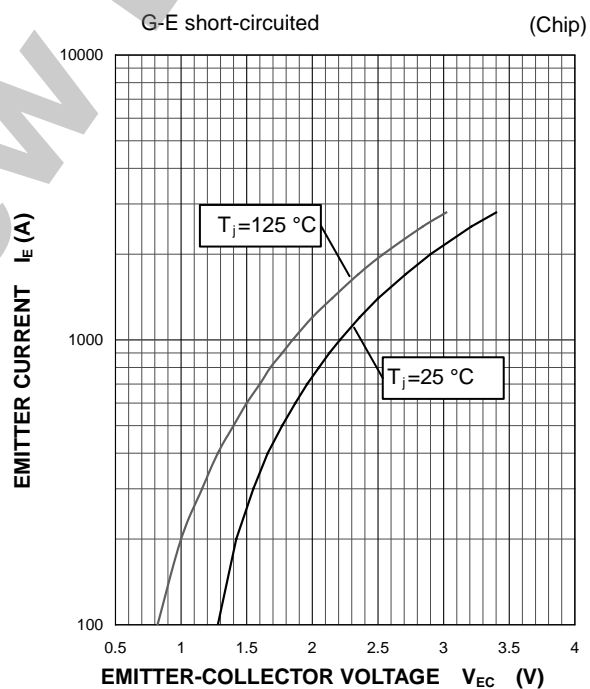
COLLECTOR-EMITTER SATURATION  
VOLTAGE CHARACTERISTICS  
(TYPICAL)



COLLECTOR-EMITTER SATURATION  
VOLTAGE CHARACTERISTICS  
(TYPICAL)



FREE WHEELING DIODE  
FORWARD CHARACTERISTICS  
(TYPICAL)



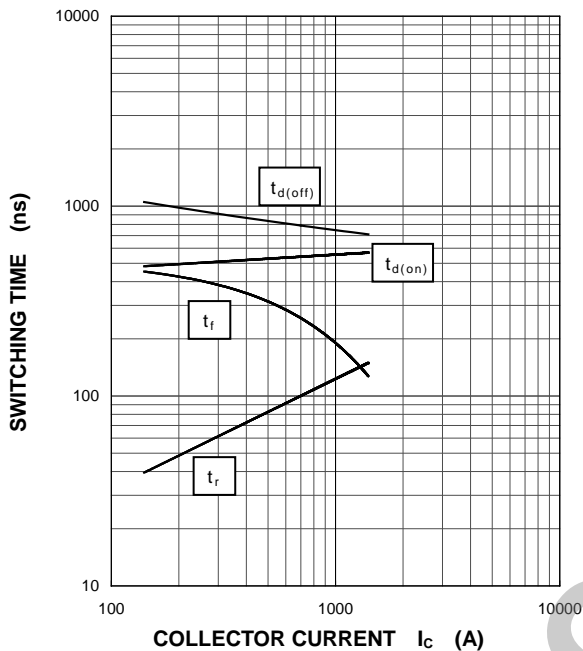
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INSULATED TYPE

## PERFORMANCE CURVES

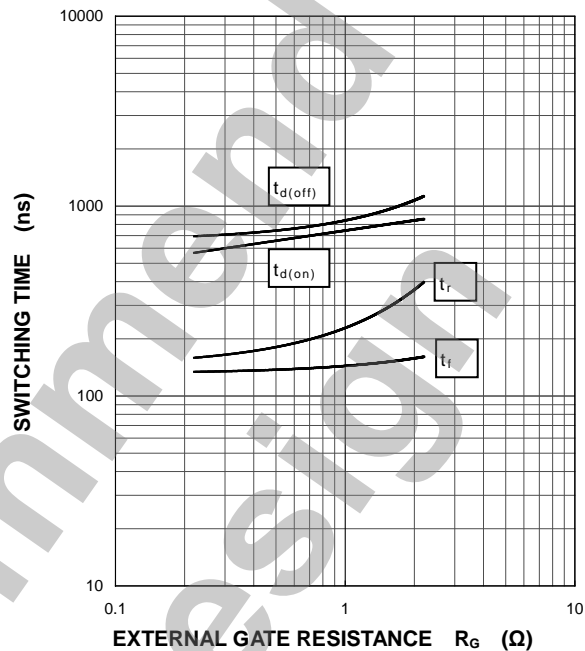
**HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)**

$V_{CC}=600\text{ V}$ ,  $V_{GE}=\pm 15\text{ V}$ ,  $R_G=0.22\ \Omega$ ,  $T_J=125\text{ }^\circ\text{C}$ ,  
INDUCTIVE LOAD



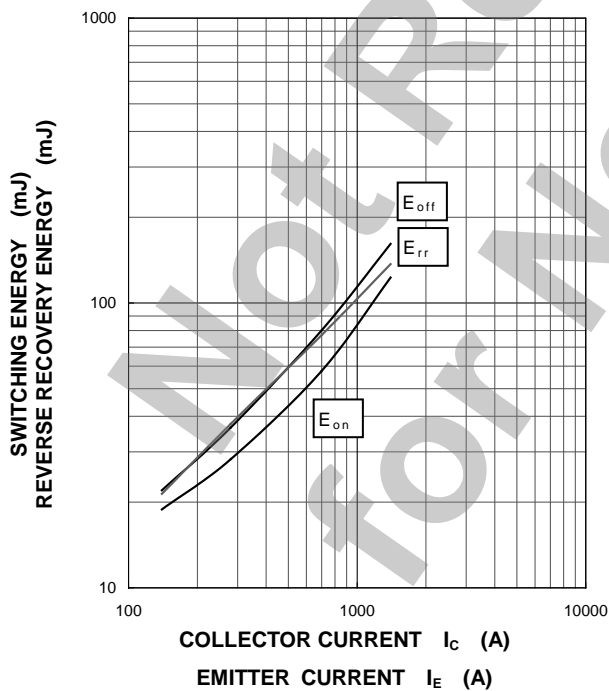
**HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)**

$V_{CC}=600\text{ V}$ ,  $I_C=1400\text{ A}$ ,  $V_{GE}=\pm 15\text{ V}$ ,  $T_J=125\text{ }^\circ\text{C}$ ,  
INDUCTIVE LOAD



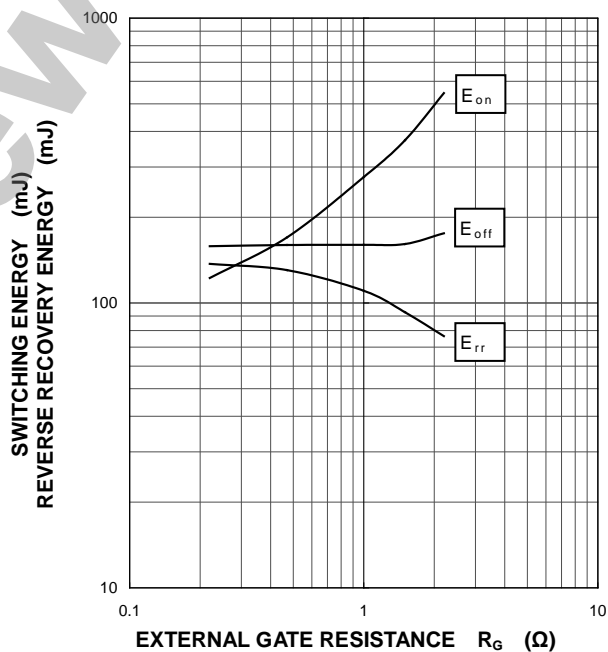
**HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)**

$V_{CC}=600\text{ V}$ ,  $V_{GE}=\pm 15\text{ V}$ ,  $R_G=0.22\ \Omega$ ,  $T_J=125\text{ }^\circ\text{C}$ ,  
INDUCTIVE LOAD, PER PULSE



**HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)**

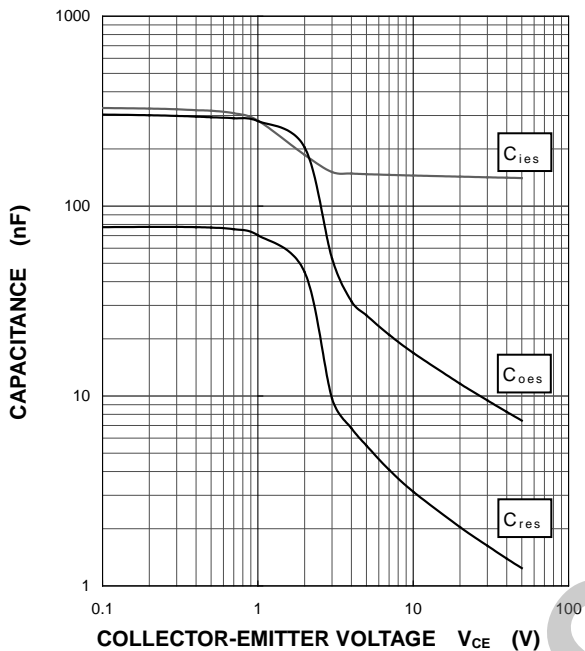
$V_{CC}=600\text{ V}$ ,  $I_C/I_E=1400\text{ A}$ ,  $V_{GE}=\pm 15\text{ V}$ ,  $T_J=125\text{ }^\circ\text{C}$ ,  
INDUCTIVE LOAD, PER PULSE



PERFORMANCE CURVES

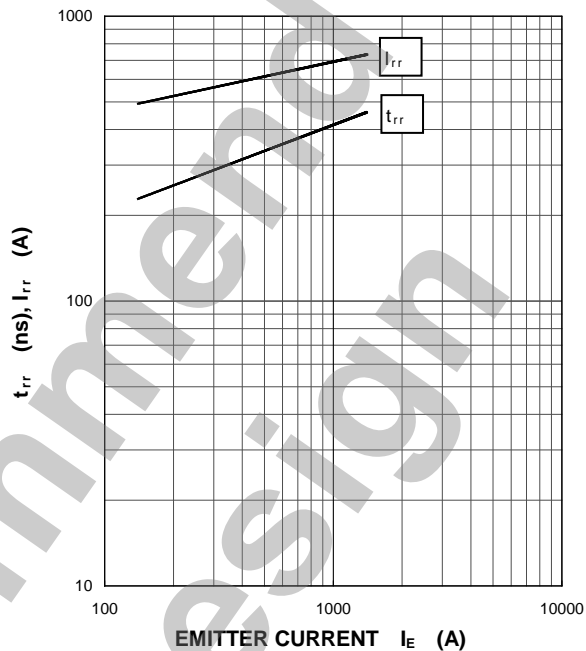
CAPACITANCE CHARACTERISTICS  
(TYPICAL)

G-E short-circuited,  $T_j=25^\circ\text{C}$



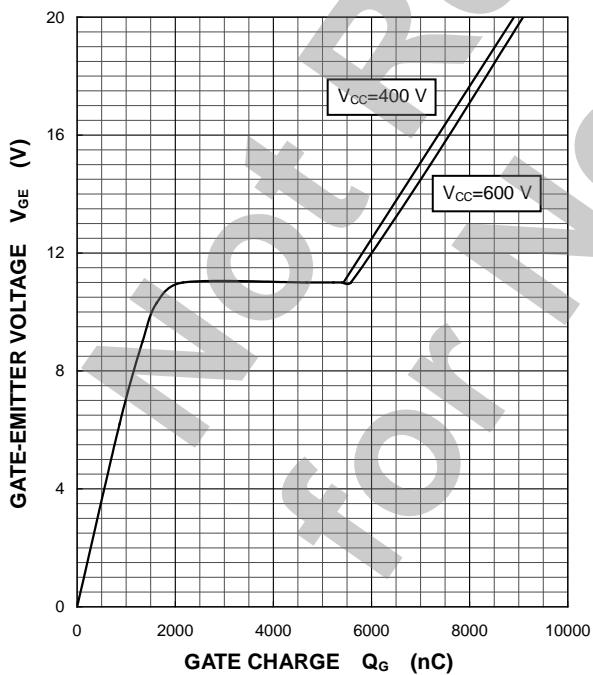
FREE WHEELING DIODE  
REVERSE RECOVERY CHARACTERISTICS  
(TYPICAL)

$V_{CC}=600\text{ V}$ ,  $V_{GE}=\pm 15\text{ V}$ ,  $R_G=0.22\ \Omega$ ,  $T_j=25^\circ\text{C}$ ,  
INDUCTIVE LOAD



GATE CHARGE CHARACTERISTICS  
(TYPICAL)

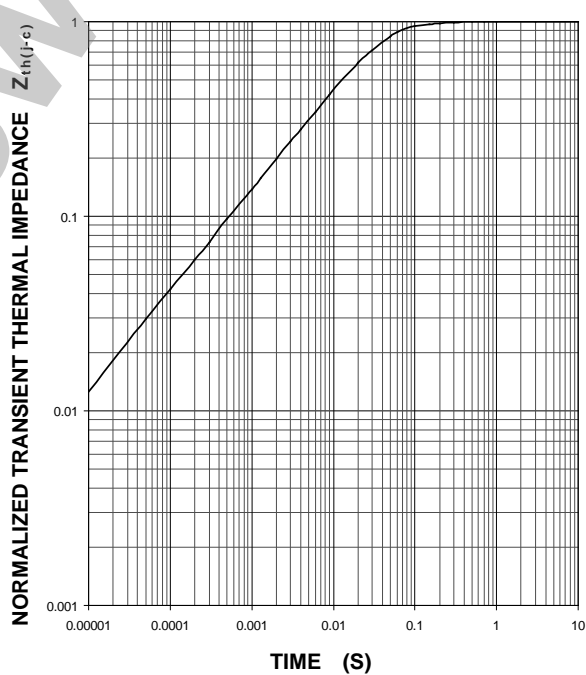
$I_C=1400\text{ A}$ ,  $T_j=25^\circ\text{C}$



TRANSIENT THERMAL IMPEDANCE  
CHARACTERISTICS  
(MAXIMUM)

Single pulse,  $T_C=25^\circ\text{C}$

$R_{th(j-c)Q}=14\text{ K/kW}$ ,  $R_{th(j-c)D}=23\text{ K/kW}$





### **Keep safety first in your circuit designs!**

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